

Notice of References Cited	Application/Control No. 09/662,358	Applicant(s)/Patent Under Reexamination NODA ET AL.	
	Examiner Anh D. Mai	Art Unit 2814	Page 1 of 1

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	W	P. Bouillon et al., Theoretical Analysis of Kink Effect in C-V Characteristics of Indium-Implanted NMOS Capacitors. IEEE 1998, pp. 19-22.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.